



BUK9Y07-30B

N-channel TrenchMOS logic level FET

Rev. 03 — 7 April 2010

Product data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|------------------------|----------------------------------|---|---------------------|-----|-----|------------------|
| V_{DS} | drain-source voltage | $T_j \geq 25 \text{ }^\circ\text{C}; T_j \leq 175 \text{ }^\circ\text{C}$ | - | - | 30 | V |
| I_D | drain current | $V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ }^\circ\text{C};$ see Figure 1 ; see Figure 4 | [1] | - | - | 75 A |
| P_{tot} | total power dissipation | $T_{mb} = 25 \text{ }^\circ\text{C}$; see Figure 2 | - | - | 105 | W |
| Static characteristics | | | | | | |
| R_{DSon} | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ }^\circ\text{C}$; see Figure 12 ; see Figure 13 | - | 4.9 | 7 | $\text{m}\Omega$ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ }^\circ\text{C}$ | - | 4 | 6 | $\text{m}\Omega$ |

Avalanche ruggedness

nexperia

Table 1. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|--|--|-----|------|-----|------|
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 75 \text{ A}$; $V_{sup} \leq 30 \text{ V}$; $R_{GS} = 50 \Omega$; $V_{GS} = 5 \text{ V}$; $T_{j(init)} = 25 \text{ }^\circ\text{C}$; unclamped | - | - | 198 | mJ |
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 5 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 24 \text{ V}$; see Figure 14 | - | 12.4 | - | nC |

[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----------------------|--------|-----------------------------------|--------------------|----------------|
| 1 | S | source | | |
| 2 | S | source | | |
| 3 | S | source | | |
| 4 | G | gate | | |
| mb | D | mounting base; connected to drain | | |
| SOT669 (LFPAK) | | | | |

3. Ordering information

Table 3. Ordering information

| Type number | Package | | | Version |
|-------------|---------|---|--|---------|
| | Name | Description | | |
| BUK9Y07-30B | LFPAK | plastic single-ended surface-mounted package (LFPAK); 4 leads | | SOT669 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit | |
|-----------------------------|--|---|---|-----|-----|------|---|
| V_{DS} | drain-source voltage | $T_j \geq 25^\circ\text{C}; T_j \leq 175^\circ\text{C}$ | - | - | 30 | V | |
| V_{DGR} | drain-gate voltage | $R_{GS} = 20\text{ k}\Omega$ | - | - | 30 | V | |
| V_{GS} | gate-source voltage | | -15 | - | 15 | V | |
| I_D | drain current | $T_{mb} = 25^\circ\text{C}; V_{GS} = 5\text{ V}$; see Figure 1 ; [1] $T_{mb} = 100^\circ\text{C}; V_{GS} = 5\text{ V}$; see Figure 1 | - | - | 75 | A | |
| I_{DM} | peak drain current | $T_{mb} = 25^\circ\text{C}; t_p \leq 10\text{ }\mu\text{s}$; pulsed; see Figure 4 | - | - | 356 | A | |
| P_{tot} | total power dissipation | $T_{mb} = 25^\circ\text{C}$; see Figure 2 | - | - | 105 | W | |
| T_{stg} | storage temperature | | -55 | - | 175 | °C | |
| T_j | junction temperature | | -55 | - | 175 | °C | |
| Source-drain diode | | | | | | | |
| I_S | source current | $T_{mb} = 25^\circ\text{C}$ | [1] | - | - | 75 | A |
| I_{SM} | peak source current | $t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25^\circ\text{C}$ | - | - | 356 | A | |
| Avalanche ruggedness | | | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $I_D = 75\text{ A}; V_{sup} \leq 30\text{ V}; R_{GS} = 50\text{ }\Omega$; $V_{GS} = 5\text{ V}; T_{j(init)} = 25^\circ\text{C}$; unclamped | - | - | 198 | mJ | |
| $E_{DS(AL)R}$ | repetitive drain-source avalanche energy | see Figure 3 | [2] [3] [4] [5] | - | - | J | |

[1] Continuous current is limited by package.

[2] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[4] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[5] Refer to application note AN10273 for further information.

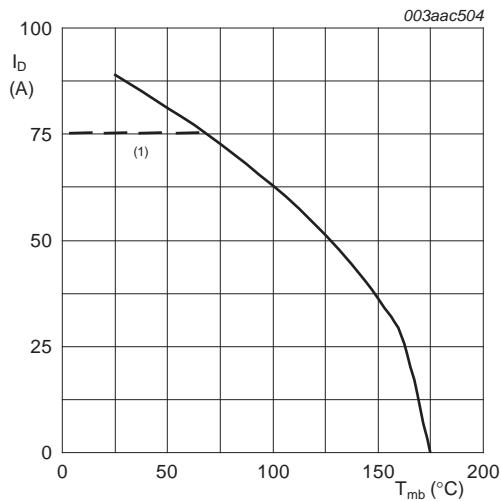
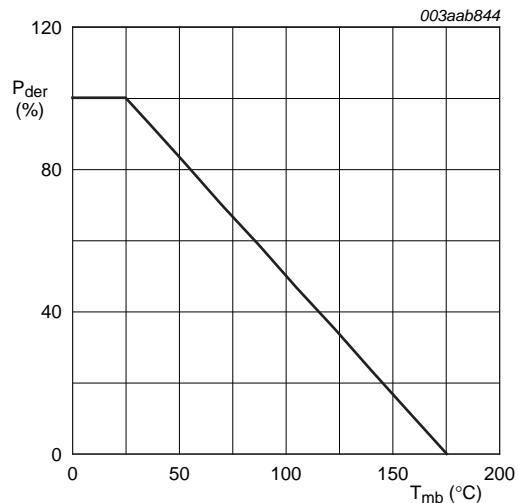


Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot}(25^\circ\text{C})} \times 100 \%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature

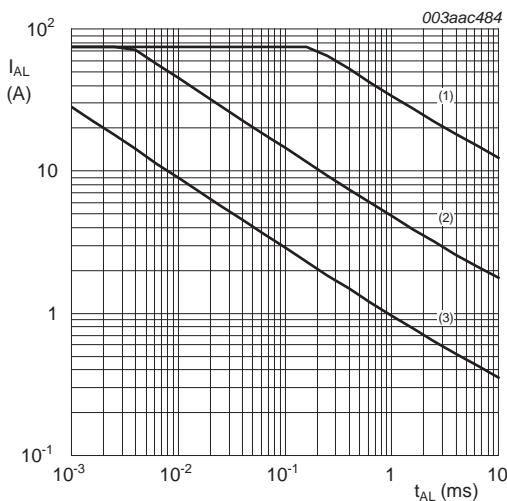
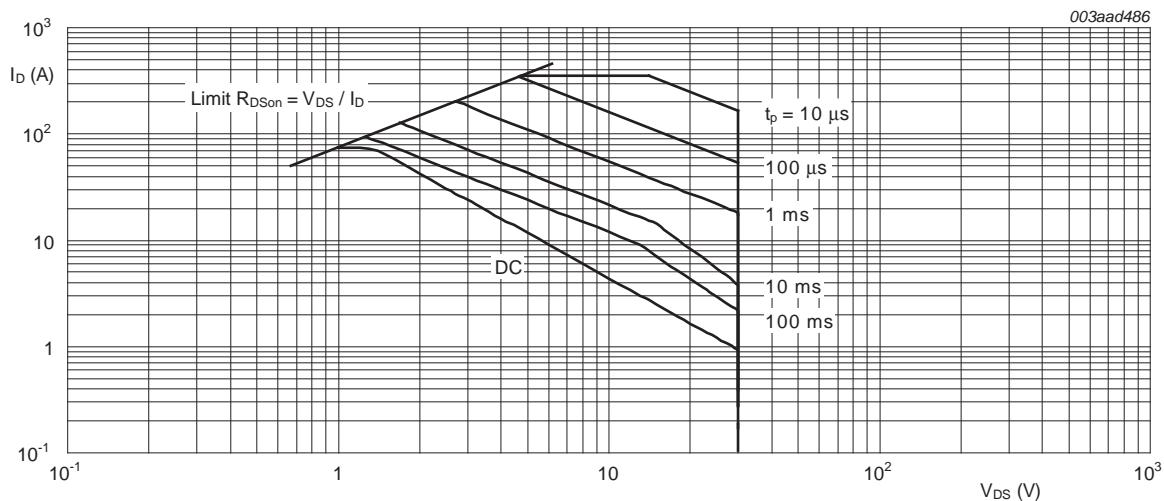


Fig 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time



$T_{mb} = 25^\circ\text{C}$; I_{DM} is single pulse

Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------------|---|------------------------------|-----|-----|------|------|
| $R_{th(j\text{-}mb)}$ | thermal resistance from junction to mounting base | see Figure 5 | - | - | 1.42 | K/W |

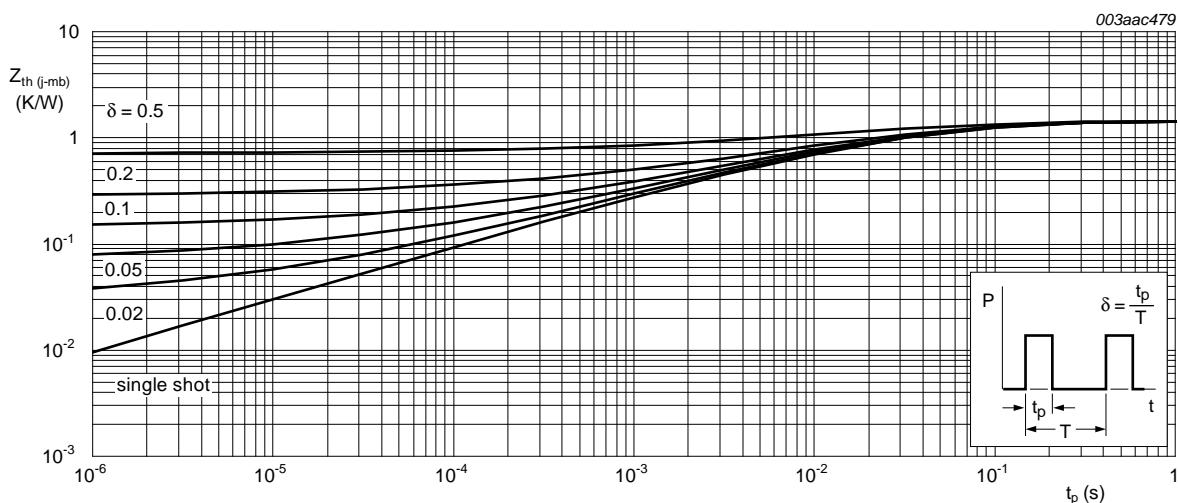
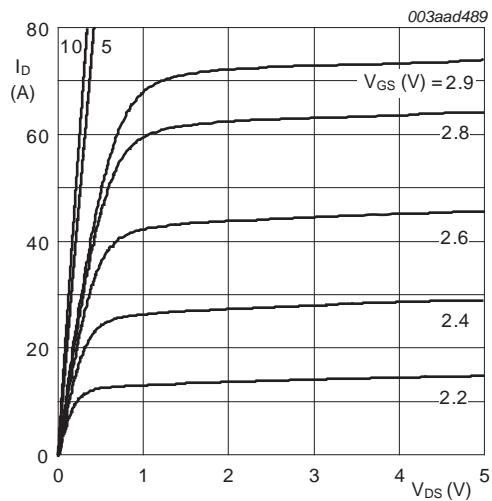


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration.

6. Characteristics

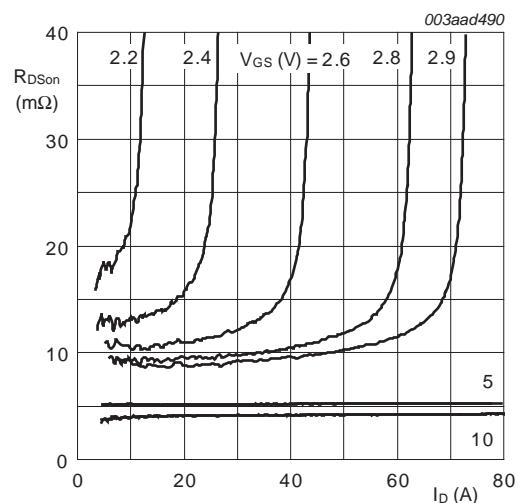
Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---|-----|------|------|------------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$ $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | 27 | - | - | V |
| $V_{GS(\text{th})}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | 1.1 | 1.5 | 2 | V |
| $V_{GSt\text{h}}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | 0.5 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11 | - | - | 2.3 | V |
| I_{DSS} | drain leakage current | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$ | - | 0.02 | 1 | μA |
| I_{GSS} | gate leakage current | $V_{DS} = 0 \text{ V}; V_{GS} = 15 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ $V_{DS} = 0 \text{ V}; V_{GS} = -15 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 2 | 100 | nA |
| $R_{DS\text{on}}$ | drain-source on-state resistance | $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 13 | - | 4.9 | 7 | $\text{m}\Omega$ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ | - | - | 8 | $\text{m}\Omega$ |
| | | $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 12 ; see Figure 13 | - | - | 13.3 | $\text{m}\Omega$ |
| | | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ }^\circ\text{C}$ | - | 4 | 6 | $\text{m}\Omega$ |
| Dynamic characteristics | | | | | | |
| $Q_{G(\text{tot})}$ | total gate charge | $I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ | - | 28.1 | - | nC |
| Q_{GS} | gate-source charge | see Figure 14 | - | 6.7 | - | nC |
| Q_{GD} | gate-drain charge | | - | 12.4 | - | nC |
| C_{iss} | input capacitance | $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ | - | 1580 | 2500 | pF |
| C_{oss} | output capacitance | $T_j = 25 \text{ }^\circ\text{C};$ see Figure 15 | - | 500 | 600 | pF |
| C_{rss} | reverse transfer capacitance | | - | 225 | 308 | pF |
| $t_{d(\text{on})}$ | turn-on delay time | $V_{DS} = 25 \text{ V}; R_L = 1 \Omega; V_{GS} = 5 \text{ V};$ | - | 25.9 | - | ns |
| t_r | rise time | $R_{G(\text{ext})} = 10 \Omega$ | - | 64.5 | - | ns |
| $t_{d(\text{off})}$ | turn-off delay time | | - | 82.3 | - | ns |
| t_f | fall time | | - | 64.8 | - | ns |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 16 | - | 0.85 | 1.2 | V |
| t_{rr} | reverse recovery time | $I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ | - | 39.3 | - | ns |
| Q_r | recovered charge | $V_{DS} = 30 \text{ V}$ | - | 53.7 | - | nC |



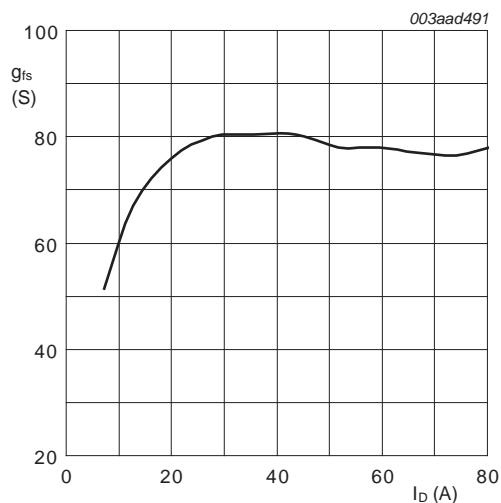
$T_j = 25^\circ C$

Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values.



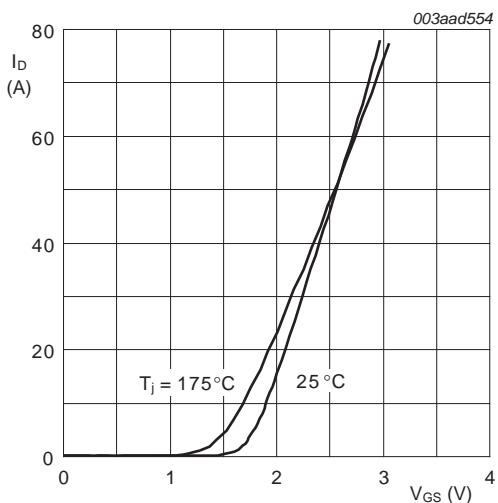
$T_j = 25^\circ C$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



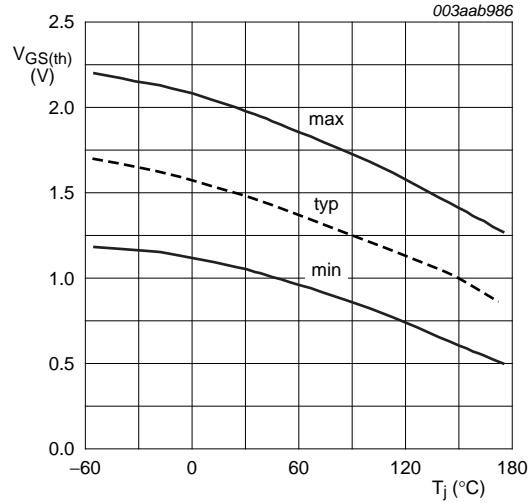
$T_j = 25^\circ C; V_{DS} = 25V$

Fig 8. Forward transconductance as a function of drain current; typical values.



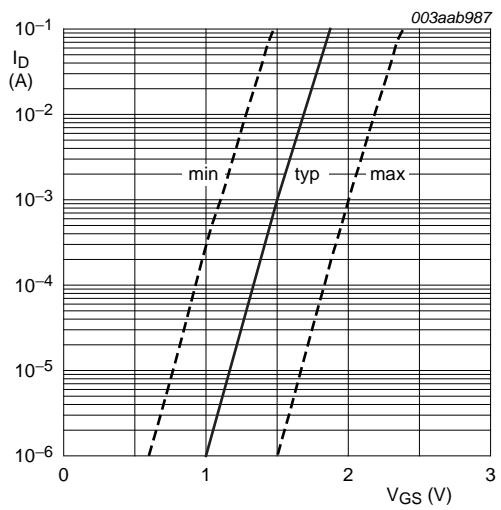
$V_{DS} = 25V$

Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



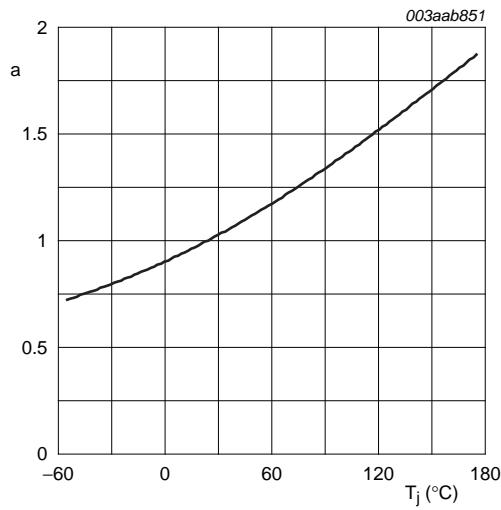
$$I_D = 1mA; V_{DS} = V_{GS}$$

Fig 10. Gate-source threshold voltage as a function of junction temperature



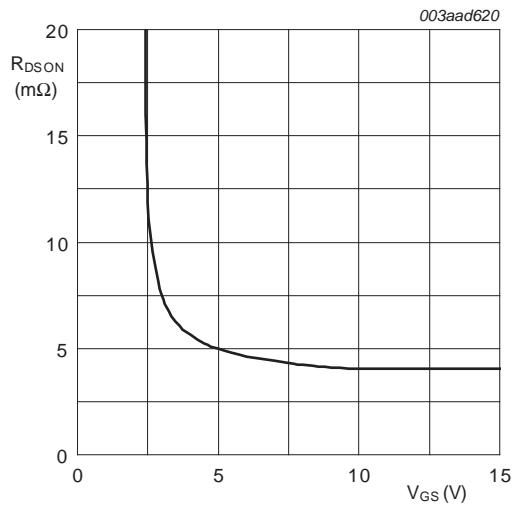
$$T_j = 25^\circ C; V_{DS} = V_{GS}$$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



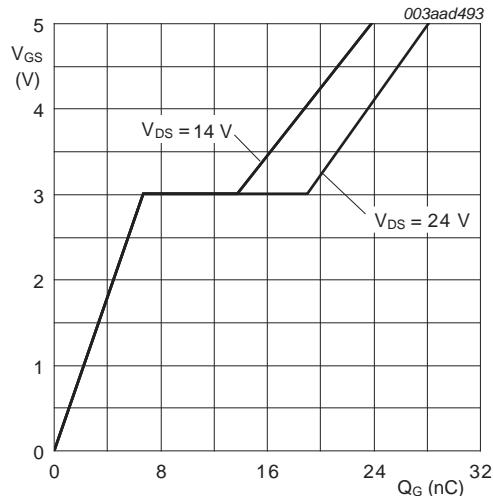
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



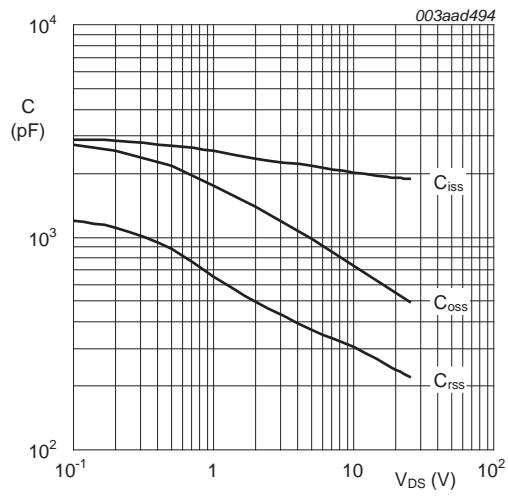
$$T_j = 25^\circ C; I_D = 25A$$

Fig 13. Drain-source on-state resistance as a function of gate-source voltage; typical values.



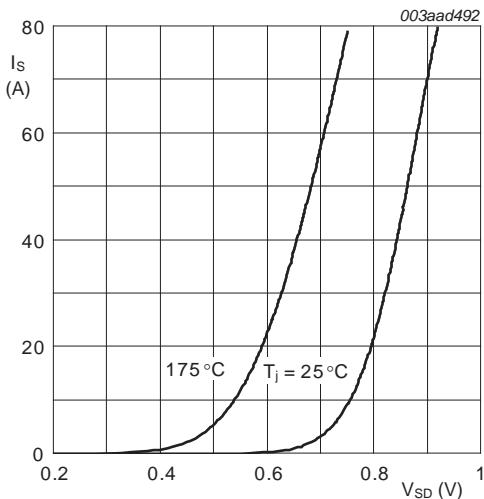
$T_j = 25^\circ C; I_D = 25A$

Fig 14. Gate-source voltage as a function of gate charge; typical values.



$V_{GS} = 0V; f = 1MHz$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$V_{GS} = 0V$

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.

7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669

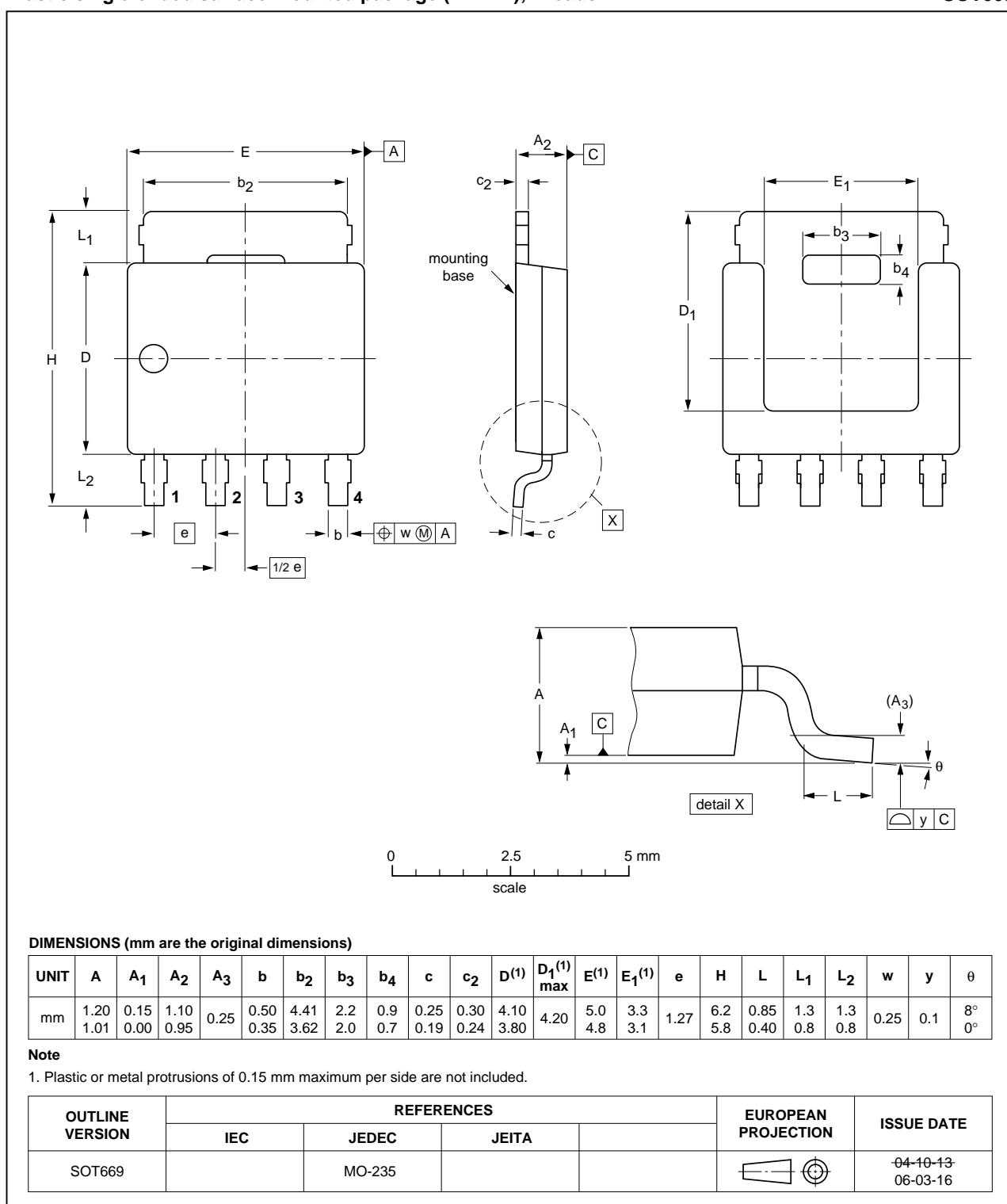


Fig 17. Package outline SOT669 (LFPAK)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------|---|---------------|---------------|
| BUK9Y07-30B_3 | 20100407 | Product data sheet | - | BUK9Y07-30B_2 |
| Modifications: | | • Status changed from objective to product. | | |
| BUK9Y07-30B_2 | 20100215 | Objective data sheet | - | BUK9Y07-30B_1 |

9. Legal information

9.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nexperia.com>.

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11. Contents

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